

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK3075

RF POWER MOSFET
FOR VHF- AND UHF-BAND POWER AMPLIFIER

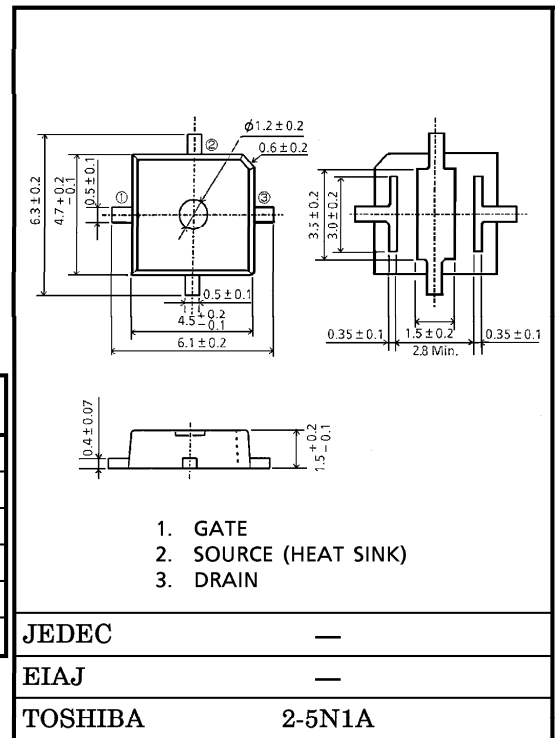
Unit in mm

- Output Power : $P_O \geq 7.5W$
- Power Gain : $G_p \geq 11.7dB$
- Drain Efficiency : $\eta_D \geq 50\%$

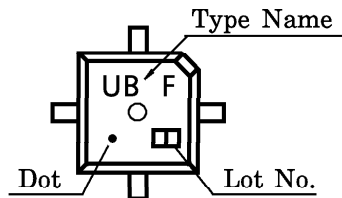
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	25	V
Drain Current	I_D	5	A
Drain Power Dissipation	P_D^*	20	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	-45~150	°C

* : $T_c=25^\circ C$ When mounted on a 1.6mm glass epoxy PCB



MARKING



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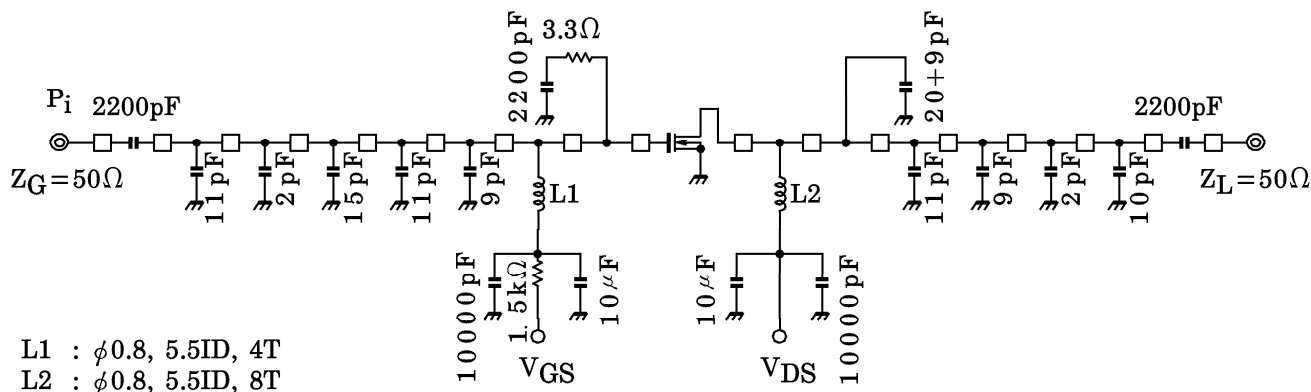
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

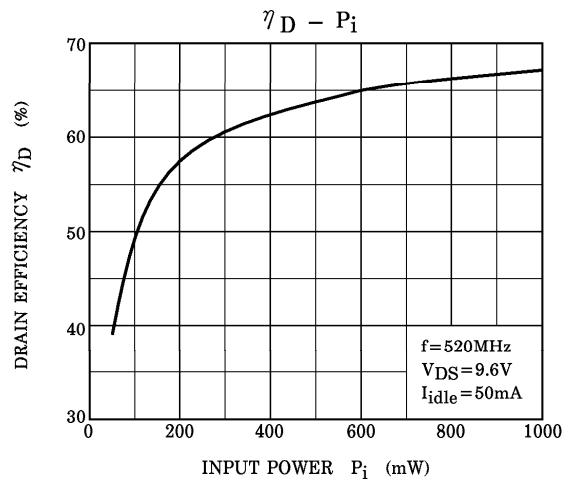
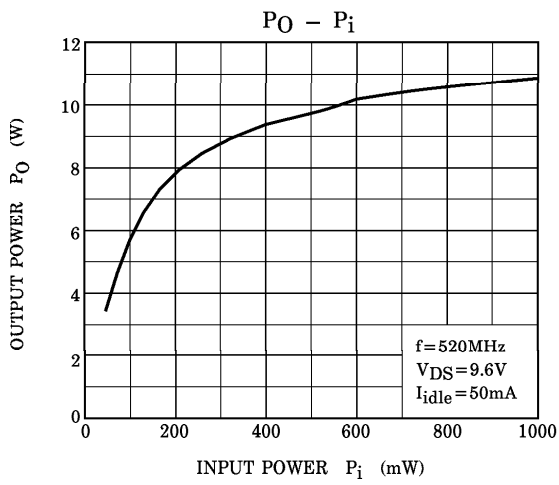
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Power	PO	V _{DS} = 9.6V	7.5	—	—	W
Drain Efficiency	η _D	I _{idle} = 50mA (V _{GS} = adjust) f = 520MHz, P _i = 500mW	50	—	—	%
Power Gain	G _P	Z _G = Z _L = 50Ω	11.7	—	—	dB
Gate Threshold Voltage	V _{th}	V _{DS} = 9.6V, I _D = 0.5mA	1.0	1.5	2.0	V
Drain Cut-off Current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0	—	—	10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = 10V, V _{DS} = 0	—	—	5	μA

HANDLING PRECAUTION

- When handling individual devices, be sure that working desks, human bodies and soldering iron are protected against electrostatic electricity.

RF OUTPUT POWER TEST FIXTURE





CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.